

1-Line Bi-directional TVS Diode

Description

The PESDU0721P1 is a bi-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU0721P1 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD protection make PESDU0721P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

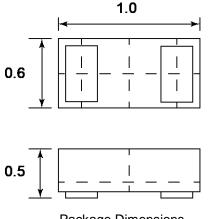
- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Operating voltage: 7V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV

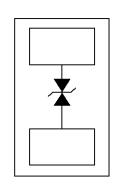
Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 5.5A (8/20µs)
- **RoHS Compliant**

Dimensions and Pin Configuration







Circuit and Pin Schematic

Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- **Digital Cameras**
- Peripherals
- **Audio Players**
- Keypads, Side Keys, LCD Displays

Marking Information



B2 = Device Marking Code

Ordering Information

Part Number	Shiping	Reel Size
PESDU0721P1	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Parameter	Symbol	Symbol Value			
Peak Pulse Power (8/20μs)	P _{PK}	60	W		
Peak Pulse Current (8/20µs)	I _{PP}	5.5	A		
ESD per IEC 61000-4-2 (Air)	V	±30	127		
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±30	- kV		
Lead temperature	TL	260	°C		
Operating Temperature Range	Тор	-40 ~ + 85	°C		
Storage Temperature Range	Тѕтс	−55 ~ + 150	°C		

Electrical Characteristics (TA=25°C unless otherwise specified)

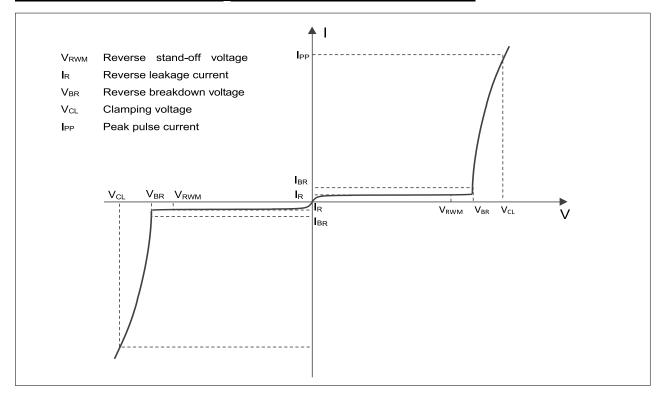
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			7	V	
Breakdown Voltage	V _{BR}	7.6	9		V	$I_T = 1 \text{mA}$
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 7V
Clamping voltage ¹⁾	V _{CL}		9.0		V	$I_{PP} = 16A, t_p = 100ns$
Dynamic resistance ¹⁾	R _{DYN}		0.25		Ω	
Clamping voltage ²⁾	V _{CL}		9.0		V	V _{ESD} = 8kV
Clamping Voltage ³⁾	Vc			9	V	I _{PP} = 1A (8/20µs pulse),
Clamping Voltage ³⁾	Vc			11	V	I _{PP} =5.5A (8/20µs pulse),
Junction Capacitance	Сл		15	21	pF	V _R = 0V, f = 1MHz

Notes:

- 1) TLP parameter: $Z0 = 50\Omega$, tp = 100ns, tr = 2ns, averaging window from 60ns to 80ns. RDYN is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.



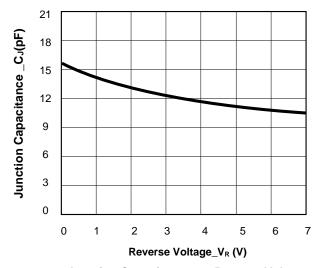
Electrical characteristics (T_A = 25°C, unless otherwise noted)



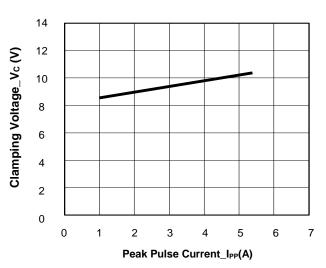
Definitions of electrical characteristics



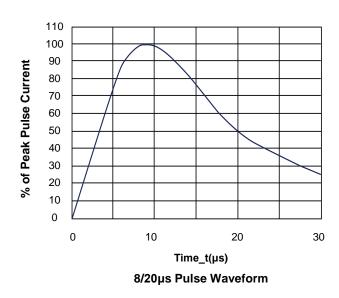
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

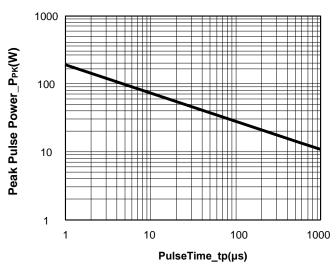


Junction Capacitance vs. Reverse Voltage

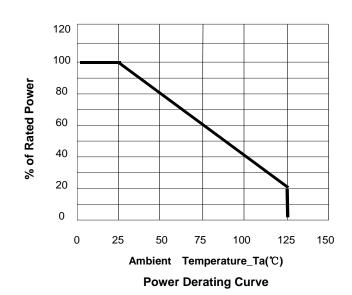


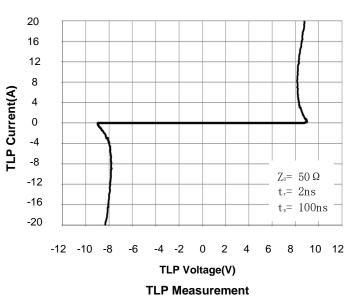
Clamping Voltage vs. Peak Pulse Current





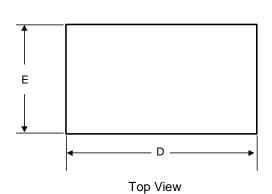
Peak Pulse Power vs. Pulse Time

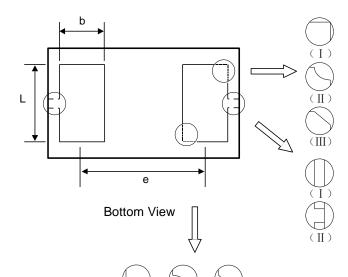


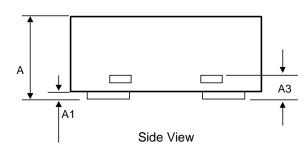




DFN1006-2 Package Outline Drawing

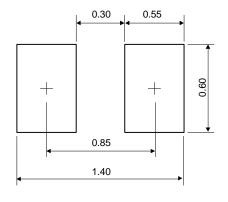






Symbol		Dimensions in Millimeters			
	Min.	Тур.	Max.		
А	0.340	0.450	0.550		
A1	0.000	0.000 0.020 0.050			
A3		0.125 Ref.			
D	0.950	1.000	1.075		
E	0.490	0.600	0.675		
b	0.200	0.250	0.300		
L	0.450	0.500	0.550		
e		0.650 BSC			

Recommended PCB Layout (Unit: mm)



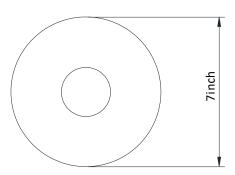
Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

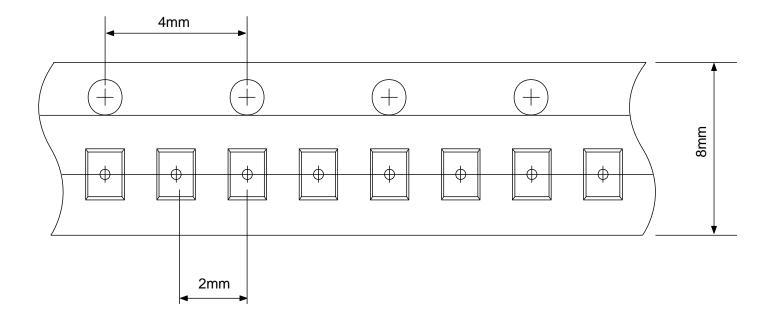


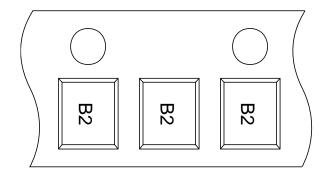
TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions







User Direction of Feed



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